

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
CHUN-HSIANG FAN	07/09/2015
CHUN-HSIUNG LIN	07/16/2015
MAO-LIN HUANG	07/15/2015
RECEIVING PARTY DATA	
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State/Country:	TAIWAN
Postal Code:	300-77
PROPERTY NUMBERS Total: 1	
Property Type	Number
Application Number:	14804032
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NAME OF SUBMITTER:	CINDY STOUTEN
SIGNATURE:	/Cindy Stouten/
DATE SIGNED:	07/21/2015
Total Attachments: 1	
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ATTORNEY DOCKET NO.
TSM15-0138

ASSIGNMENT

WHEREAS, I, the undersigned inventor (or one of the undersigned joint inventors), of residence as listed, having invented certain new and useful improvements as below entitled, for which application for United States Letters Patent is made; and

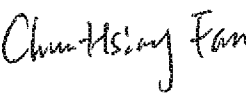
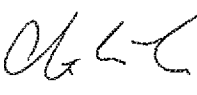
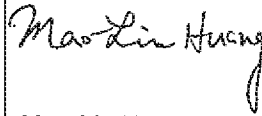
WHEREAS, Taiwan Semiconductor Manufacturing Company, Ltd. ("Assignee"), a corporation organized and existing under the laws of Taiwan, the Republic of China, with its principal office at No. 8, Li-Hsin Rd. 6 Science-Based Industrial Park, Hsin-Chu 300-77 Taiwan, R.O.C., is desirous of acquiring my entire right, title and interest in and to said invention, and to said application and any Letters Patent that may issue thereon in the United States and all other countries throughout the world;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, I hereby sell and assign to said Assignee, its successors and assigns, my entire right, title and interest in and to said invention and in and to said application and all patents which may be granted therefor, and all future non-provisional applications including divisions, reissues, substitutions, continuations, and extensions thereof; and I hereby authorize and request the Commissioner for Patents to issue all patents for said invention, or patent resulting therefrom, insofar as my interest is concerned, to said Assignee, as assignee of my entire right, title and interest. I declare that I have not executed and will not execute any agreement in conflict herewith.

I also hereby sell and assign to Assignee, its successors and assigns, my foreign rights to the invention disclosed in said application, in all countries of the world, including, but not limited to, the right to file applications and obtain patents under the terms of the International Convention for the Protection of Industrial Property, and of the European Patent Convention, and further agree to execute any and all patent applications, assignments, affidavits, and any other papers in connection therewith necessary to perfect such patent rights.

I hereby further agree that I will communicate to said Assignee, or to its successors, assigns, and legal representatives, any facts known to me respecting said invention or the file history thereof, and at the expense of said Assignee, its legal representatives, successors, or assigns, will testify in any legal proceedings, sign all lawful papers, execute all divisional, continuation, reissue and substitute applications, make all lawful oaths, and generally do everything possible to aid said Assignee, its legal representatives, successors, and assigns, to obtain and enforce proper patent protection for said invention in all countries.

IN WITNESS WHEREOF, I hereunto set my hand and seal this day and year;

TITLE OF INVENTION	Source/Drain Regions for High Electron Mobility Transistors (HEMT) and Methods of Forming Same			
SIGNATURE OF INVENTOR AND NAME	 Chun-Hsiang Fan	 Chun-Hsiung Lin	 Mao-Lin Huang	
DATE	7.9.2015	7.16.2015	07.15.2015	
RESIDENCE	Hsinchu, Taiwan	Zhubei City, Taiwan	Hsinchu, Taiwan	